

Schottky barrier diode

RB520G-30

●Applications

Low current rectification

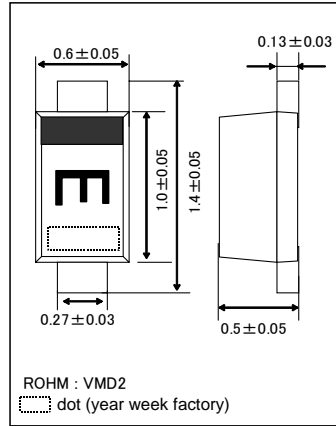
●Features

- 1) Ultra Small mold type. (VMD2)
- 2) Low I_R .
- 3) High reliability.

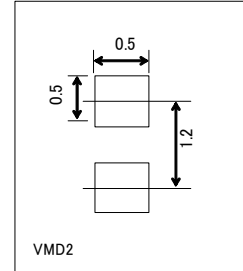
●Construction

Silicon epitaxial planar

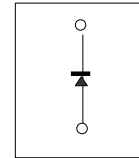
●Dimensions (Unit : mm)



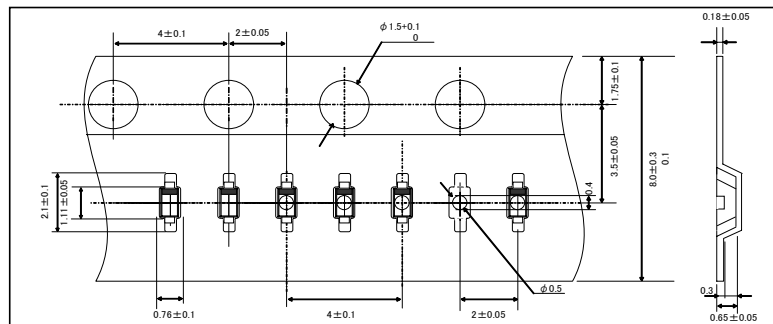
● Land size figure (Unit : mm)



●Structure



●Taping specifications (Unit : mm)



●Absolute maximum ratings ($T_a=25^\circ\text{C}$)

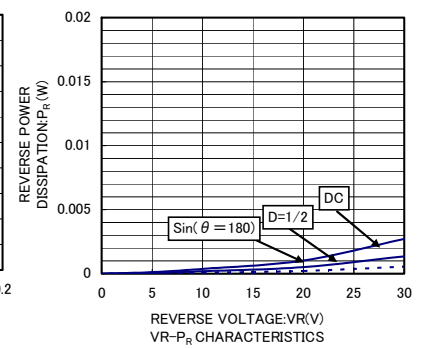
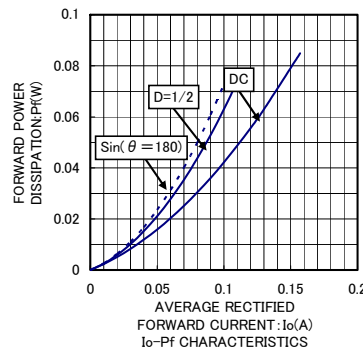
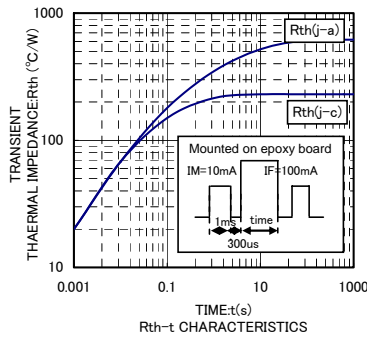
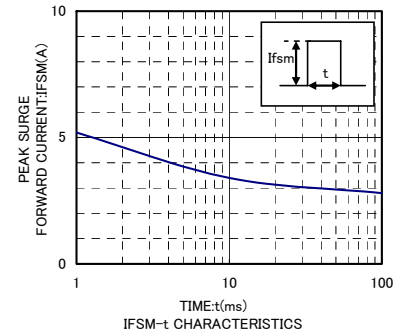
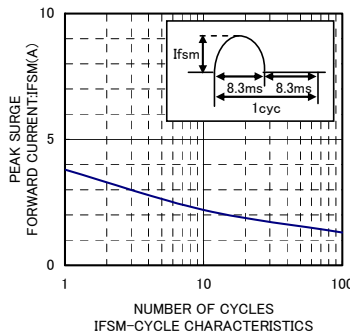
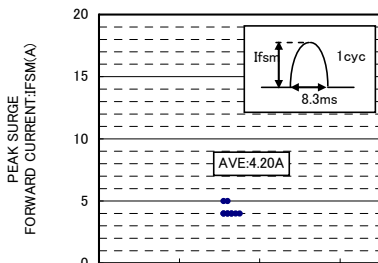
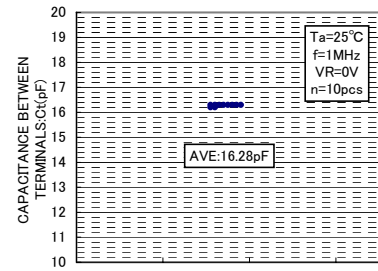
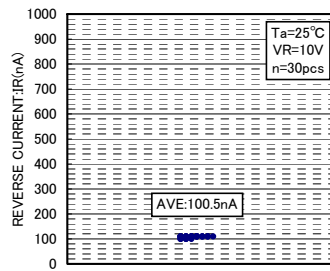
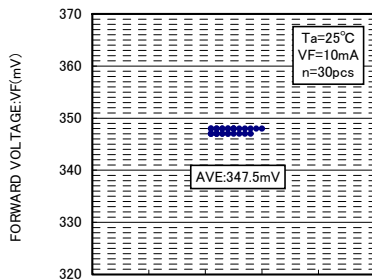
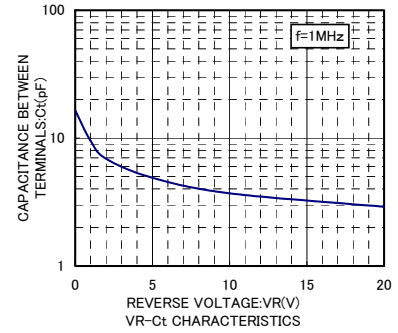
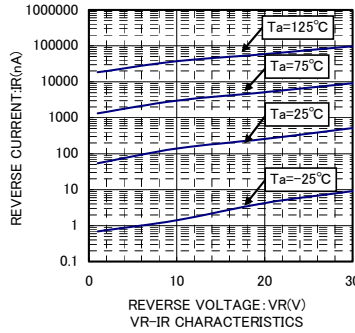
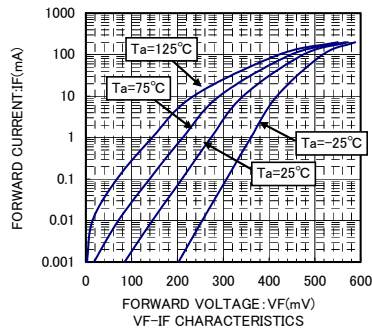
Parameter	Symbol	Limits	Unit
Reverse voltage(DC)	V_R	30	V
Average rectified forward current	I_o	100	mA
Forward current surge peak (60Hz·1cyc)	I_{FSM}	500	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +125	$^\circ\text{C}$

●Electrical characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.45	V	$I_F=10\text{mA}$
Reverse current	I_R	-	-	0.5	μA	$V_R=10\text{V}$

Diodes

●Electrical characteristic curves (Ta=25°C)



Diodes

